PD-95736

International TOR Rectifier

 $\mathsf{HEXFRED}^\mathsf{m}$

HFA08TB120PbF

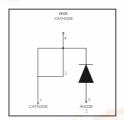
Ultrafast, Soft Recovery Diode

Features

- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- Specified at Operating Conditions
- · Lead-Free

Benefits

- · Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- · Reduced Parts Count



 $V_R = 1200V$ $V_F (typ.)^* = 2.4V$ $I_{F (AV)} = 8.0A$ $Q_{rr} (typ.) = 140nC$ $I_{RRM} (typ.) = 4.5A$ $t_{rr} (typ.) = 28ns$ $r_{rec} M / dt (typ.)^* = 85A / \mu s$



Description

International Rectifier's HFA08TB120 is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 volts and 8 amps continuous current, the HFA08TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_RRM) and does not exhibit any tendency to "snap-off" during the $t_{\rm b}$ portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

Absolute Maximum Ratings

	Parameter	Max	Units
V _R	Cathode-to-Anode Voltage	1200	V
I _F @ T _C = 100°C	Continuous Forward Current	8.0	А
I _{FSM}	Single Pulse Forward Current	130	
I _{FRM}	Maximum Repetitive Forward Current	32	
P _D @ T _C = 25°C	Maximum Power Dissipation	73.5	W
$P_D @ T_C = 100^{\circ}C$	Maximum Power Dissipation	29	
TJ	Operating Junction and	- 55 to 150	°C
T _{STG}	Storage Temperature Range		

*125°C

www.irf.com

1 10/18/04



International

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)IGR Rectifier

	Parameter	Min	Тур	Max	Units	Test Conditions
V _{BR}	Cathode Anode Breakdown	1200	-	-	V	I _R = 100μA
	Voltage					
V _{FM}	Max. Forward Voltage	-	2.6	3.3	V	I _F = 8.0A
		-	3.4	4.3		I _F = 16A
		-	2.4	3.1		I _F = 8.0A, T _J = 125°C
I _{RM}	Max. Reverse Leakage	-	0.31	10	μА	$V_R = V_R$ Rated
	Current	-	135	1000		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ Rated
C _T	Junction Capacitance	-	11	20	рF	V _R = 200V
Ls	Series Inductance	-	8.0	-	nΗ	Measured lead to lead 5mm from pkg body

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

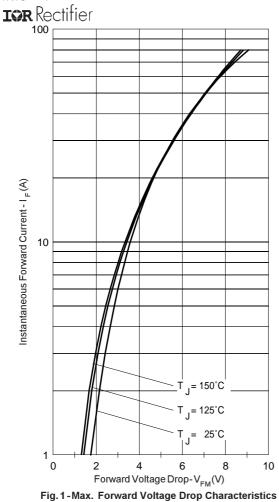
Parameter		Min	Тур	Max	Units	Test Conditions		
t _{rr}	Reverse Recovery Time	-	28	-	ns	$I_F = 1.0A$, $di_f/dt = 200A/\mu s$, $V_R = 30V$		
t _{rr1}		-	63	95		T _J = 25°C	I _F = 8.0A	
t _{rr2}		-	106	160		T _J = 125°C	V _R = 200V	
I _{RRM1}	Peak Recovery Current	-	4.5	8.0	Α	T _J = 25°C	$di_f/dt = 200A/\mu s$	
I _{RRM2}		-	6.2	11		T _J = 125°C		
Q _{rr1}	Reverse Recovery Charge	-	140	380	nC	$T_J = 25^{\circ}C$		
Q _{rr2}		-	335	880		T _J = 125°C		
di _{(rec)M} /dt1 Peak Rate of Recovery		-	133	-	A/µs	T _J = 25°C		
di _{(rec)M} /dt2 Current During t _b		-	85	-		T _J = 125°C		

Thermal - Mechanical Characteristics

	Parameter	Min	Тур	Max	Units
T _{lead} ①	Lead Temperature	-	-	300	°C
R _{thJC}	Thermal Resistance, Junction to Case	-	-	1.7	k/W
R _{thJA} ②	Thermal Resistance, Junction to Ambient	-	-	40	
R _{thCS}	Thermal Resistance, Case to Heat Sink	-	0.25	-	
Wt	Weight	-	6.0	-	g
		-	0.21	-	(oz)
	Mounting Torque	6.0	-	12	Kg-cm
		5.0	-	10	lbf•in

 ^{0.063} in. from Case (1.6mm) for 10 sec
 Typical Socket Mount
 Mounting Surface, Flat, Smooth and Greased





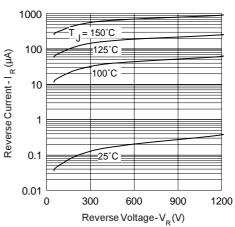


Fig. 2-Typ. Values Of Reverse Current . Vs. Reverse Voltage

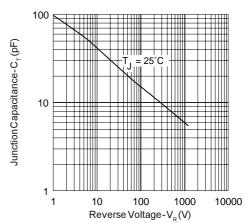


Fig. 3-Typical Junction Capacitance Vs. Reverse Voltage

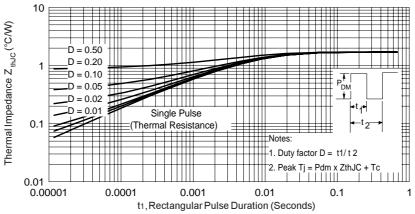
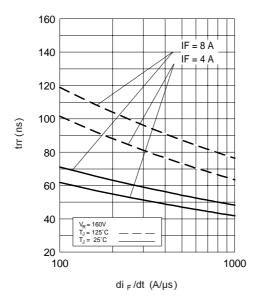
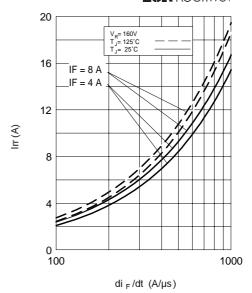


Fig. 4-Max. Thermal Impedance Z_{thJC} Characteristics

International Rectifier



 $\begin{array}{c} \text{Fig. 5-Typical Reverse Recovery} \\ \text{Vs. di}_{\text{f}}/\text{dt} \end{array}$



 $\begin{array}{ccc} \text{Fig.6-Typical} & \text{Recovery Current} \\ & \text{Vs. di}_{\text{f}}/\text{dt} \end{array}$

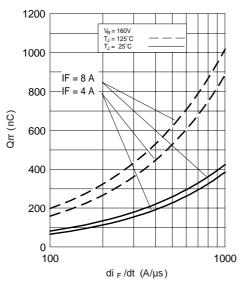


Fig. 8 - Typical Stored Charge vs. di_f/dt

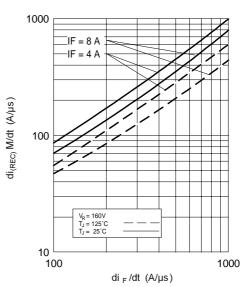


Fig. 7 - Typical $di_{(REC)}$ M/dt vs. di_f /dt

International Rectifier

Reverse Recovery Circuit

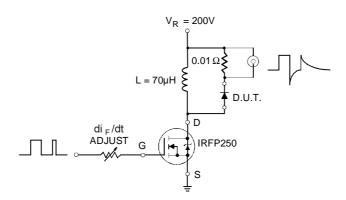
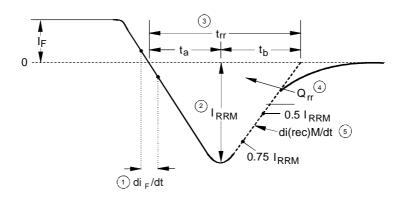


Fig. 9- Reverse Recovery Parameter Test Circuit



- 1. di_F/dt Rate of change of current through zero crossing
- 2. IRRM Peak reverse recovery current
- $\rm 3.\,t_{ff}$ Reverse recovery time measured from zero crossing point of negative going IF to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current
- 4. $\rm Q_{rr}$ Area under curve defined by t $_{rr}$ and $\rm I_{RRM}$

Q
$$rr = \frac{t_{rr} \times l_{RRM}}{2}$$

5. di (rec) M / dt - Peak rate of change of current during t $_{D}$ portion of t $_{TT}$

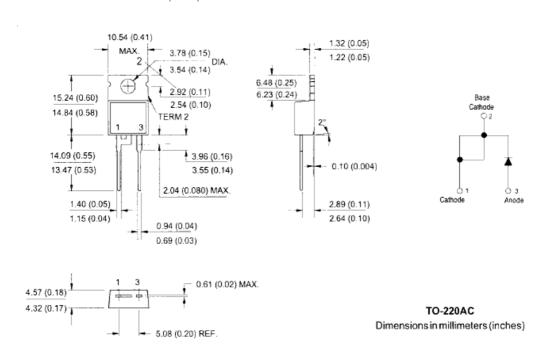
Fig. 10 - Reverse Recovery Waveform and Definitions

www.irf.com 5

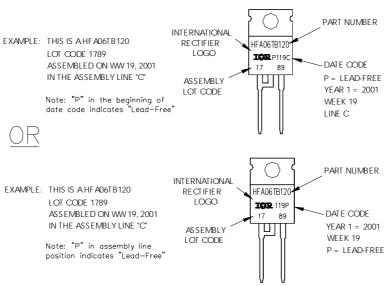
International TOR Rectifier

TO-220AC Package Outline

Dimensions are shown in millimeters (inches)



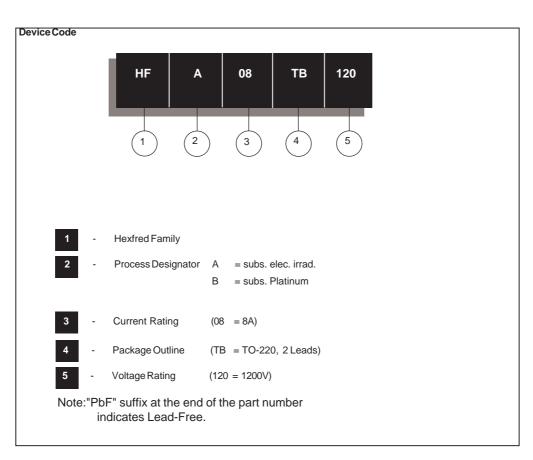
TO-220AC Part Marking Information



6 www.irf.com



Ordering Information Table



Data and specifications subject to change without notice.

